

PRELIMINARY

DP8402A/DP8403/DP8404/DP8405 32-Bit Parallel Error Detection and Correction Circuits (EDAC's)

General Description

The DP8402A, DP8403, DP8404 and DP8405 devices are 32-bit parallel error detection and correction circuits (EDACs) in 52-pin DP8402A and DP8403 or 48-pin DP8404 and DP8405 600-mil packages. The EDACs use a modified Hamming code to generate a 7-bit check word from a 32-bit data word. This check word is stored along with the data word during the memory write cycle. During the memory read cycle, the 39-bit words from memory are processed by the EDACs to determine if errors have occurred in memory.

Single-bit errors in the 32-bit data word are flagged and corrected.

Single-bit errors in the 7-bit check word are flagged, and the CPU sends the EDAC through the correction cycle even though the 32-bit data word is not in error. The correction cycle will simply pass along the original 32-bit data word in this case and produce error syndrome bits to pinpoint the error-generating location.

Double bit errors are flagged but not corrected. These errors may occur in any two bits of the 39-bit word from memory (two errors in the 32-bit data word, two errors in the 7-bit check word, or one error in each word). The gross-error condition of all lows or all highs from memory will be detected. Otherwise, errors in three or more bits of the 39-bit word are beyond the capabilities of these devices to detect.

Read-modify-write (byte-control) operations can be performed with the DP8402A and DP8403 EDACs by using output latch enable, LEDBO, and the individual OEB0 thru OEB3 byte control pins.

Diagnostics are performed on the EDACs by controls and internal paths that allow the user to read the contents of the DB and CB input latches. These will determine if the failure occurred in memory or in the EDAC.

Features

- Detects and corrects single-bit errors
- Detects and flags double-bit errors
- Built-in diagnostic capability
- Fast write and read cycle processing times
- Byte-write capability ... DP8402A and DP8403
- Fully pin and function compatible with TI's SN74ALS632A thru SN74ALS635 series

System Environment





Mode	e Def	initic	ons			PCC Pin	Definition	ns DP840	2A
MODE F		ME DE	SCRIPTION			pin 1	V _{CC}	pin 35	OECB
	S1 S	0	MODE	OPE	RATION	2	LEDBO	36	CB3
0	LL	. WRI	TE		ord and output		MERR	37	CB2
				checkword		4	ERR	38	CB1
1	L F	I DIAG	GNOSTICS	•	is data words	5	DB0	39	CB0
				against lato		6	DB1	40	DB16
					output valid	7	DB2	41	DB17
2	нц	REA	D & FLAG	error flags.	ord and output		NC	42	NC
2			Duilhu	error flags	ord and output	9	NC	43	NC
3	н н	I COF	RECT		out data and	10	NC	44	DB18
-				checkword		10	DB3	45	DB10
				corrected d	ata and	12	DB3 DB4	46	DB20
				syndrome of	ode	12	DB4 DB5	40	DB21
						13	OEBO	48	OEB2
Pin D	efini	tions	5			14	DB6	40	DB22
S0, S1				de, see prec	eding				
		-	efinitions			16	DB7	50	DB23
			for 32 bit da			17	GND	51	GND
CB0 thru				ckword. Also		18	GND	52	GND
			rrection mod	e error code	auring	19	DB8	53	DB24
OEB0 th				ie. Ifer enable. V	Vhen high	20	DB9	54	DB25
OEB3				TRI-STATE		21	OEB1	55	OEB3
(DP8402				OEB0 contr		22	DB10	56	DB26
DP8403				trols DB8 th		23	DB11	57	DB27
		OEB2 c	ontrols DB1	6 thru DB23 a	and OEB3	24	DB12	58	DB28
		controls	DB24 thru [DB31.		25	DB13	59	NC
LEDBO				tch enable. \		26	DB14	60	NC
(DP8402				e Latch. Opei	ates on all	27	NC	61	NC
DP8403)			of the dataw		0 1	28	NC	62	NC
OEDB (DP8404			igh output bu	for the data I.	O port.	29	NC	63	DB29
DP8404		TRI-ST/		mers are at		30	DB15	64	DB30
OECB				uffer enable.	When	31	NC	65	DB31
0200			•	ers are in TR		32	CB6	66	S0
		mode.	••••		•••••	33	CB5	67	S1
ERR		Single e	rror output f	lag, a low ind	icates at	34	CB4	68	V _{CC}
		least a s	single bit erro	or.					
MERR				flag, a low ir	ndicates				
		two or n	nore errors p	resent.					
				Т	ABLE I. Write C	Control Function			
Memory Cycle		DAC ction	Control S1 S0	Data I/O	DB Control OEBn or OEDB	DB Output La DP8402A, DP8 LEDBO		CB Control OECB	Error Flags ERR MERR
Write		erate k word	LL	Input	н	x	Output check bits		нн

†See Table II for details on check bit generation.

DP8402A/ DP8403/ DP8404/ DP8405

Memory Write Cycle Details

During a memory write cycle, the check bits (CB0 thru CB6) are generated internally in the EDAC by seven 16-input parity generators using the 32-bit data word as defined in Table

2. These seven check bits are stored in memory along with the original 32-bit data word. This 32-bit word will later be used in the memory read cycle for error detection and correction.

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Check Word		32-Bit Data Word																												
Bit	31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5 4	1 3	2	1
CB0	Х		Х	Х		X					Х		Х	Х	Х			Х			Х		Х	х	х	x	>			
CB1				х		х		Х		Х		Х		Х	Х	Х				Х		Х		Х		Х	>	(Х
CB2	X		Х			х	х		Х			Х	Х			Х	Х		Х			Х	Х		Х		>	$\langle \rangle$	(X	
CB3			Х	х	Х				Х	Х	Х				Х	Х			Х	Х	Х				Х	Х	х			Х
CB4	X	Х							Х	х	Х	Х	Х	х			х	х							Х	Х	x >	()	(X	
CB5	X	Х	х	х	Х	х	х	Х									х	х	Х	Х	Х	х	Х	Х						
CB6	X I	Х	х	X	X	х	X	X																	х	х	хx	$\langle \rangle$	< X	х

The seven check bits are parity bits derived from the matrix of data bits as indicated by "X" for each bit.

Check bits 0, 1, 2 are odd parity or the exclusive NORing of the "X"ed bits for the particular check bit. Check bits 3, 4, 5, 6 are even parity or the exclusive ORing of the "X"ed bits for the particular check bit.

Memory Read Cycle (Error Detection & Correction Details)

During a memory read cycle, the 7-bit check word is retrieved along with the actual data. In order to be able to determine whether the data from the memory is acceptable to use as presented on the bus, the error flags must be tested to determine if they are at the high level.

The first case in Table III represents the normal, no-error conditions. The EDAC presents highs on both flags. The

next two cases of single-bit errors give a high on MERR and a low on ERR, which is the signal for a correctable error, and the EDAC should be sent through the correction cycle. The last three cases of double-bit errors will cause the EDAC to signal lows on both ERR and MERR, which is the interrupt indication for the CPU.

TABLE III. Error Function

	TADLE III. EITU	Funct	1011	
Total Numb	er of Errors	Erro	r Flags	Data Correction
32-Bit Data Word	7-Bit Check Word	ERR	MERR	Data Correction
0	0	н	н	Not applicable
1	0	L	н	Correction
0	1	L	н	Correction
1	1	L	L	Interrupt
2	0	L	L	Interrupt
0	2	L	L	Interrupt

The DP8402 check bit syndrome matrix can be seen in TA-BLE II. The horizontal rows of this matrix generate the check bits by selecting different combinations of data bits, indicated by "X"s in the matrix, and generating parity from them. For instance, parity check bit "0" is generated by EXCLUSIVE NORing the following data bits together; 31, 29, 28, 26, 21, 19, 18, 17, 14, 11, 9, 8, 7, 6, 4, and 0. For example, the data word "0000001H" would generate the check bits CB6-0 = 48H (Check bits 0, 1, 2 are odd parity and check bits 3, 4, 5, 6 are even parity).

During a WRITE operation (mode 0) the data enters the DP8402 and check bits are generated at the check bit input/output port. Both the data word and the check bits are then written to memory. During a READ operation (mode 2, error detection) the data and check bits that were stored in memory, now possibly in error, are input through the data and check bit I/O ports. New check bits are internally generated from the data word. These new check bits are then compared, by an EXCLU-SIVE NOR operation, with the original check bits that were stored in memory. The EXCLUSIVE NOR of the original check bits, that were stored in memory, with the new check bits is called the syndrome word. If the original check bits are the same as the new check bits, a no error condition, then a syndrome word of all ones is produced and both error flags (ERR and MERR) will be high. The DP8402 matrix encodes errors as follows:

Memory Cycle	EDAC Function	Cor S1	ntrol S0	Data I/O	DB Control OEBn or OEDB	DB Output Latch DP8402A, DP8403 LEDBO	Check I/O	CB Control OECB	Error Flags ERR MERR
Read	Read & flag	н	L	Input	н	X	Input	Н	Enabled†
Read	Latch input data and check bits	н	н	Input data latched	н	L	Input check word latched	н	Enabled†
Read	Output corrected data & syndrome bits	н	н	Output corrected data word	L	x	Output syndrome bits‡	L	Enabled†

TABLE IV. Read, Flag, and Correct Function

Memory Read Cycle (Error Detection & Correction Details) (Continued)

1) Single data bit errors cause 3 or 5 bits in the syndrome word to go low. The columns of the check bit syndrome matrix (TABLE II) are the syndrome words for all single bit data errors in the 32 bit word (also see TABLE V). The data bit in error corresponds to the column in the check bit syndrome matrix that matches the syndrome word. For instance, the syndrome word indicating that data bit 31 is in error would be (CB6-CB0) = "0001010", see the column for data bit 31 in TABLE II, or see TABLE V. During mode 3 (S0 = S1 = 1) the syndrome word is decoded, during single data bit errors, and used to invert the bit in error thus correcting the data word. The corrected word is made available on the data I/O port (DB0 thru DB31), the check word I/O port (CB0 thru CB6) presents the 7-bit syndrome error code. This syndrome error code can be used to locate the bad memory chip.

- 2) A single check bit error will cause that particular check bit to go low in the syndrome word.
- 3) A double bit error will cause an even number of bits in the syndrome word to go low. The syndrome word will then be the EXCLUSIVE NOR of the two individual syndrome words corresponding to the 2 bits in error. The two-bit error is not correctable since the parity tree can only identify single bit errors.

If any of the bits in the syndrome word are low the "ERR" flag goes low. The "MERR" (dual error) flag goes low during any double bit error conditions. (See Table III).

Three or more simultaneous bit errors can cause the EDAC to believe that no error, a correctable error, or an uncorrectable error has occurred and will produce erroneous results in all three cases. It should be noted that the gross-error conditions of all lows and all highs will be detected.

TABLE V. Syndrome Decoding

Syndrome Bits	Error	Ιſ	s	yn	droi	ne	Bits	;	Error	Г	S	yn	dro	om	e E	lits		Error			Syı	ndr	om	e B	lits		Error
6543210	EIIO	•	6 !	5 4	1 3	2	1	0	EIIUI	6	3 9	5	4	3	2	1	0	EIIO		6	5	4	3	2	1	0	EIIU
LLLLLL	unc	Γ	LH	+ 1	. L	L	L	L	2-bit	F	1 1	L	L	L	L	L	L	2-bit		н	н	L	L	L	L	L	unc
L L L L L L H	2-bit	I	LH	1 1	. L		L	н	unc	_ ⊦	1 1	L	L	L	L	L	н	unc		н	н	L	L	L	L	н	2-bit
	2-bit	L		I I				L	DB7	۱ŀ		LI		_	L		L	unc		н	Н		L	L		L	2-bit
<u> </u>	unc	լլ		11	<u> </u>	L	Н	н	2-bit	브		L	L	L	L	н	н	2-bit		н	н	L	L	L	н	Н	DB23
LLLLHLL	2-bit	I	Lŀ	11	. L	н	L	L	DB6	- [H	1 1	L	L	L	н	L	L	unc		н	н	L	L	Н	L	L	2-bit
	unc	L				н			2-bit							L		2-bit		н	н			н			DB22
	unc				. L		Н		2-bit	- (F		L				Н		2-bit		Н	Η			Н		L	DB21
LLLLHHH	2-bit	ιμ				H	н	н	DB5	브			_			н		unc		H	н			н		н	2-bit
LLLHLLL	2-bit				-	L	L	L	DB4	- U.			_		_	L	_	unc		н	н			L		L	2-bit
LLLHLLH	unc				. н		L		2-bit							L		2-bit		H	Н			L			DB20
	DB31					L		L	2-bit							н		2-bit		н	н			L		L	DB19
	2-bit					L			DB3	- H	-		-			н	-	DB15	ľ	Н		L				п	2-bit
	unc	I I '				н		L	2-bit							L		2-bit		Н	Н			н		L	DB18
	2-bit 2-bit					Н Н			DB2	F		L				L		unc DB14		н	н	L		н	_		2-bit 2-bit
	DB30	- I ⁻				H			unc 2-bit							H H		2-bit	i	Н		L				L	
										- H			_				_										
	2-bit				1 L		L	L	DB0			L L				L		unc		н		н		L	L	L	2-bit DB16
	unc DB29			4 F 4 F	4 L 4 L	-	н		2-bit 2-bit	F F			H H					2-bit 2-bit		H H		H H	L	L			unc
	2-bit				1 L		н		unc							н		DB13				н		L			2-bit
	DB28	Η				н			2-bit	- H							_	2-bit		_		н				_	DB17
	2-bit				1 L 1 L			L H	DB1				H			L L		2-01 DB12		н	н	н	L		L		2-bit
	2-bit					н		Ľ	unc	ļ,						н		DB11		н		н		н			2-bit
LLHLHHH	DB27					н		_	2-bit	ا						н		2-bit		н		н					CB3
	DB26				нн		L	1	2-bit	F			н	н	1	L	1	2-bit		н	н	н	н	1			unc
	2-bit						_	_	unc	ļ,						L		DB10		н		н					2-bit
	2-bit					L		Ľ	unc	⊦					Ĺ		Ľ	DB9		н		н		_	_	Ľ	2-bit
LLHHLHH	DB25					L		н	2-bit	F						н	н	2-bit		н		н				н	CB2
	2-bit				н н	н	L	L	unc	F	-	L	н	н	н	L	L	DB8		н	н	н	н	н	L	L	2-bit
	DB24					н			2-bit							L		2-bit		н	н			н		_	CB1
LLHHHHL	unc	i				н			2-bit	H						H		2-bit		н	н			н			CB0
LLНННН	2-bit	I	LI			н			CB6	H						н		CB5		н	н	н	н	н	н	н	none
CB X = error in check bit																			•								

DB Y = error in data bit Y

2-bit = double-bit error

unc = uncorrectable multibit error

MEMORY		CON			15	DB OUTPUT		СВ	EPPO	RFLAG	
CYCLE	EDAC FUNCTION	S1	S0	BYTEn†	OEB n†	LEDBO	CHECK I/O	CONTROL		MERR	
Read	Read & Flag	н	L	Input	н	X	Input	н	Ena	bled	
Read	Latch input data & check bits	н	н	input data latched	н	L	Input check word latched	н	Ena	bled	
	Latch corrected			Output			Hi-Z	н			
Read	data word into output latch	н	н	data word latched	н	н	Output Syndrome bits	L	Enabled		
Modify	Modify appropriate byte or bytes &	1	L	Input modified BYTE0	н	н	Output	L	н	н	
/write	generate new check word	generate new	L	L	Ouput unchanged BYTE0	L		check word		11	п

TOEB0 controls DB0-DB7 (BYTE0), OEB1 controls DB8-DB15 (BYTE1), OEB2 controls DB16-DB23 (BYTE2), OEB3 controls DB24-DB31 (BYTE3).

Read-Modify-Write (Byte Control) Operations

The DP8402A and DP8403 devices are capable of bytewrite operations. The 39-bit word from memory must first be latched into the DB and CB input latches. This is easily accomplished by switching from the read and flag mode (S1 = H, SO = L) to the latch input mode (S1 = H, S0 = H). The EDAC will then make any corrections, if necessary, to the data word and place it at the input of the output data latch. This data word must then be latched into the output data latch by taking LEDBO from a low to a high.

Byte control can now be employed on the data word through the $\overline{OEB0}$ through $\overline{OEB3}$ controls. $\overline{OEB0}$ controls DB0-DB7 (byte 0), $\overline{OEB1}$ controls DB8-DB15 (byte 1), $\overline{OEB2}$ controls DB16-DB23 (byte 2), and $\overline{OEB3}$ controls DB24-DB31 (byte 3). Placing a high on the byte control will disable the output and the user can modify the byte. If a low is placed on the byte control, then the original byte is allowed to pass onto the data bus unchanged. If the original data word is altered through byte control, a new check word must be generated before it is written back into menoy. This is easily accomplished by taking control S1 and S0 low. Table VI lists the read-modify-write functions.

Diagnostic Operations

The DP8402A thru DP8405 are capable of diagnostics that allow the user to determine whether the EDAC or the memory is failing. The diagnostic function tables will help the user to see the possibilities for diagnostic control.

In the diagnostic mode (S1 = L, S0 = H), the checkword is latched into the input latch while the data input remains transparent. This lets the user apply various data words against a fixed known checkword. If the user applies a diagnostic data word with an error in any bit location, the ERR flag should be low. If a diagnostic data word with two errors in any bit location is applied, the MERR flag should be low. After the checkword is latched into the input latch, it can be verified by taking OECB low. This outputs the latched checkword. With the DP8402A and DP8403, the diagnostic data word can be latched into the output data latch and verified. It should be noted that the DP8404 and DP8405 do not have this pass-through capability because they do not contain an output data latch. By changing from the diagnostic mode (S1 = L, S0 = H) to the correction mode (S1 = H, S0 = H), the user can verify that the EDAC will correct the diagnostic data word. Also, the syndrome bits can be produced to verify that the EDAC pinpoints the error location. Table VII DP8402A and DP8403 and Table VIII DP8404 and DP8405 list the diagnostic functions.

			TABLE VII. DP	·····	·				
EDAC FUNCTION	CON		DATA I/O	DB BYTE CONTROL	DB OUTPUT LATCH	CHECK I/O	CB CONTROL	ERROF	FLAGS
LEACTONCTION	S1	S 0		OEBn	LEDBO		OECB	2.111	
Read & flag	н	L	Input correct data word	н	х	Input correct check bits	н	н	н
Latch input check word while data input latch remains transparent	L	н	Input diagnostic data word†	н	L	Input check bits latched	н	Ena	bled
Latch diagnostic data word into	L	н	Input diagnostic	н	н	Output latched check bits	L	Ena	bled
output latch			data word†			Hi-Z	н		
Latch diagnostic data word into input latch	н	н	Input diagnostic data word	н	н	Output syndrome bits	L	Ena	bled
mpuriation			latched			Hi-Z	н		
Output diagnostic data word &	н	н	Output diagnostic	L	н	Output syndrome bits	L	Ena	bled
syndrome bits			data word			Hi-Z	н		
Output corrected diagnostic data word & output	н	н	Output corrected diagnostic	L	L	Output syndrome bits	L	Ena	bled
syndrome bits			data word			Hi-Z	н		

† Diagnostic data is a data word with an error in one bit location except when testing the MERR error flag. In this case, the diagnostic data word will contain errors in two bit locations.

TABLE VIII. DP8404, DP8405 Diagnostic Function

				· ., · · · · · ·				
EDAC FUNCTION	CON S1	TROL S0	DATA I/O	DB CONTROL	CHECK I/O	DB CONTROL	ERROF	FLAGS
Read & flag	н	L	Input correct data word	н	Input correct check bits	н	н	н
Latch input check bits while data input latch remains transparent	L	н	Input diagnostic data word†	н	Input check bits latched	Н	Ena	abled
Output input check bits	L	н	Input diagnostic data word†	н	Output input check bits	L	Ena	abled
Latch diagnostic data into	н	н	Input diagnostic	н	Output syndrome bits	L	Fn	abled
input latch			data word latched		Hi-Z	н	211	
Output corrected diagnostic	н	н	Output corrected diagnostic	L	Output syndrome bits	L	Ena	abled
data word			data word		Hi-Z	н		

†Diagnostic data is a data word with an error in one bit location except when testing the MERR error flag. In this case, the diagnostic data word will contain errors in two bit locations.



DP8402A HAS TRI-STATE (\bigtriangledown) CHECK-BIT AND DATA OUTPUTS. DP8403 HAS OPEN-COLLECTOR (\bigcirc) CHECK-BIT AND DATA OUTPUTS.

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TL/F/8535~4



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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Over Operating Free-Air Temperature Range (unless otherwise noted)

Supply Voltage, V _{CC} (See Note 1)	7V	Operating Free-A
Input Voltage: CB and DB	5.5V	
All Others	7V	Storage Tempera

Operating Free-Air Temperature	e: Military - 55	°C to + 125°C
	Commercial	0° to +70°C
Storage Temperature Range	-65	°C to +150°C

Recommended Operating Conditions

Symbol	Parameter	Conditions		Militar	У	Co	mme	rcial	Units
Cymbol	T drameter	Conacions	Min	Тур	Max	Min	Тур	Max	Onito
V _{CC}	Supply Voltage		4.5	5	5.5	4.5	5	5.5	v
ViH	High-Level Input Voltage		2			2			v
VIL	Low-Level Input Voltage				0.8			0.8	v
ЮН	High-Level Output Current	ERR Or MERR			-0.4			-0.4	mA
ЮН		DB Or CB DP8402A, DP8404			-1			-2.6	
IOL	Low-Level Output Current	ERR Or MERR			4			8	mA
UL		DB or CB			12			24	1
t _w	Pulse Duration	LEDBO Low	25			25			ns
		 (1) Data And Check Word Before S0 ↑ (S1 = H) 	15			10			
		(2) SO High Before $\overline{\text{LEDBO}} \uparrow (S1 = H)^{\dagger}$	45			45			j
		(3) $\overline{\text{LEDBO}}$ High Before The Earlier of S0 \downarrow or S1 \downarrow †	0			0			
t _{su}	Setup Time	(4) $\overline{\text{LEDBO}}$ High Before S1 \uparrow (S0 = H)	0			0			ns
		(5) Diagnostic Data Word Before S1 ↑ (S0 = H)	15			10			ļ
		(6) Diagnostic Check Word Before The Later Of S1 \downarrow or S0 \uparrow	15			10			ļ
I		(7) Diagnostic Data Word Before LEDBO ↑ (S1 = L and S0 = H)‡	25			20			
		(8) Read-Mode, S0 Low And S1 High	35			30			
		(9) Data And Check Word After S0↑ (S1 = H)	20			15			
•.	Hold Time	(10) Data Word After S1 \uparrow (S0 = H)	20			15			ne
t _h		(11) Check Word After The Later of S1↓ or S0↑	20			15			ns
		(12) Diagnostic Data Word After LEDBO↑ (S1 = L And S0 = H)‡	0			0			
t _{corr}	Correction Time (see Figure	e 1)*	65			58			ns
TA	Operating Free-Air Temper	ature	- 55	{	125	0		70	°C

*This specification may be interpreted as the maximum delay to guarantee valid corrected data at the output and includes the t_{su} setup delay.

†These times ensure that corrected data is saved in the output data latch.

 $\ddagger \mbox{These}$ times ensure that the diagnostic data word is saved in the output data latch.

DP8402A, DP8404 Electrical Characteristics Over Recommended Operating Free-Air Temperature Range (unless otherwise noted)

Completed	Demonstra			Military		Co	mmerci	al	
Symbol	Parameter	Test Conditions	Min	Typ†	Max	Min	Typ†	Max	Units
VIK		$V_{CC} = 4.5V, I_{I} = -18 \text{ mA}$			-1.5			- 1.5	v
	All outputs	$V_{CC} = 4.5V$ to 5.5V, $I_{OH} = -0.4$ mA	V _{CC} -2			V _{CC} -2			
V _{OH}	DD as CD	$V_{CC} = 4.5V, I_{OH} = -1 \text{ mA}$	2.4	3.3					v
	DB or CB	$V_{\rm CC} = 4.5 V, I_{\rm OH} = -2.6 \rm mA$				2.4	3.2		
		$V_{\rm CC} = 4.5 V, I_{\rm OL} = 4 {\rm mA}$		0.25	0.4		0.25	0.4	
.,	ERR or MERR	$V_{CC} = 4.5V, I_{OL} = 8 \text{ mA}$					0.35	0.5	
VOL	DB er CB	$V_{CC} = 4.5V, I_{OL} = 12 \text{ mA}$		0.25	0.4		0.25	0.4	V
	DB or CB	$V_{\rm CC} = 4.5 V, I_{\rm OL} = 24 \rm mA$					0.35	0.5	
	S0 or S1	$V_{\rm CC} = 5.5 V, V_{\rm I} = 7 V$			0.1			0.1	
ц 	All others	$V_{\rm CC} = 5.5 V, V_1 = 5.5 V$			0.1			0.1	mA
	S0 or S1				20			20	
ŀн	All others‡	$V_{\rm CC} = 5.5 V, V_{\rm I} = 2.7 V$			20			20	μΑ
	S0 or S1				-0.4			-0.4	
կլ	All others‡	$V_{\rm CC} = 5.5 V, V_{\rm I} = 0.4 V$			-0.1			-0.1	mA
l _O §		$V_{\rm CC} = 5.5 V, V_{\rm O} = 2.25 V$	-30		-112	-30		-112	mA
ICC		V _{CC} = 5.5V, (See Note 1)		150	250		150	250	mA

DP8403, DP8405 Electrical Characteristics

Over Recommended Operating Free-Air Temperature Range (unless otherwise noted)

Symbol				Military		Co			
	Parameter	Test Conditions	Min	Typ†	Max	Min	Typ†	Max	Units
VIK		$V_{CC} = 4.5V, I_{I} = -18 \text{ mA}$			- 1.5			- 1.5	V
V _{OH}	ERR or MERR	$V_{CC} = 4.5V$ to 5.5V, $I_{OH} = -0.4$ mA	V _{CC} -2			V _{CC} -2			v
ЮН	DB or CB	$V_{CC} = 4.5V, V_{OH} = 5.5V$			0.1			0.1	mA
	ERR or MERR	$V_{CC} = 4.5V, I_{OL} = 4 \text{ mA}$		0.25	0.4		0.25	0.4	v
		$V_{CC} = 4.5 V, I_{OL} = 8 \text{ mA}$					0.35	0.5	
V _{OL}	DB or CB	$V_{\rm CC} = 4.5 V, I_{\rm OL} = 12 \rm mA$		0.25	0.4		0.25	0.4	
		$V_{CC} = 4.5V, I_{OL} = 24 \text{ mA}$					0.35	0.5	
	S0 or S1	$V_{CC} = 5.5V, V_{I} = 7V$							
կ	All others	$V_{CC} = 5.5V, V_{I} = 5.5V$							mA
	S0 or S1								
lΉ	All others‡	$V_{\rm CC} = 5.5 V, V_{\rm I} = 2.7 V$							μΑ
IIL	S0 or S1								
	All others‡	$V_{CC} = 5.5V, V_{I} = 0.4V$							mA
l _O §	ERR or MERR	$V_{CC} = 5.5V, V_{O} = 2.25V$	-30		-112	-30		-112	mA
Icc		V _{CC} = 5.5V, (See Note 1)		150			150		mA

†All typical values are at V_{CC} = 5V, T_A = +25°C.

 \ddagger For I/O ports (QA through QH), the parameters I_{IH} and I_{IL} include the off-state output current.

\$The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, IOS.

Note 1: I_{CC} is measured with S0 and S1 at 4.5V and all CB and DB pins grounded.

DP8402A Switching Characteristics $V_{CC} = 4.5V$ to 5.5V, $C_L = 50$ pF, $T_A = Min$ to Max (unless otherwise noted)

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Symbol	From	То	Test Conditions	Mili	itary	Com	Units	
Symbol	(Input)	(Output)		Min	Max	Min	Max	
t	DB and CB	ERR	$S1 = H, S0 = L, R_L = 500\Omega$	10	43	10	40	ns
^t pd	DB	ERR	$S1 = L, S0 = H, R_L = 500\Omega$	10	43	10	40	
t _{pd}	DB and CB	MERR	$S1 = H, S0 = L, R_L = 500\Omega$	15	67	15	55	ns
	DB	MERR	$S1 = L, S0 = H, R_L = 500\Omega$	15	67	15	55	
t _{pd}	S0↓ and S1↓	СВ	$R1 = R2 = 500\Omega$	10	60	10	48	ns
t _{pd}	DB	СВ	$S1 = L, S0 = L, R1 = R2 = 500\Omega$	10	60	10	48	ns
t _{pd}	LEDB0 1	DB	$S1 = X, S0 = H, R1 = R2 = 500\Omega$	7	35	7	30	ns
t _{pd}	S1 ↑	СВ	$S0 = H, R1 = R2 = 500\Omega$	10	60	10	50	ns
t _{en}	OECB 1	СВ	$S0 = H, S1 = X, R1 = R2 = 500\Omega$	2	30	2	25	ns
t _{dis}	OECB↑	СВ	$S0 = H, S1 = X, R1 = R2 = 500\Omega$	2	30	2	25	ns
t _{en}	OEB0 thru OEB3↓	DB	$S0 = H, S1 = X, R1 = R2 = 500\Omega$	2	30	2	25	ns
t _{dis}	OEB0 thru OEB3 ↑	DB	$S0 = H, S1 = X, R1 = R2 = 500\Omega$	2	30	2	25	ns

DP8403 Switching Characteristics V_{CC} = 4.5V to 5.5V, C_L = 50 pF, T_A = Min to Max (unless otherwise noted)

	From	To (Output)	Test Conditions	Military			Commercial			Units
Symbol	(input)			Min	Typ†	Max	Min	Typ†	Max	Units
t- a	DB and CB	ERR	$S1 = H, S0 = L, R_L = 500\Omega$		26			26		ns
t _{pd}	DB	ERR	$S1 = L, S0 = H, R_L = 500\Omega$		26			26		115
		MERR	$S1 = H, S0 = L, R_L = 500\Omega$		40			40		
t _{pd}	DB and CB		$S1 = L, S0 = H, R_L = 500\Omega$		40			40		ns
t _{pd}	S0 \downarrow and S1 \downarrow	СВ	$R_L = 680\Omega$		40			40		ns
t _{pd}	DB	СВ	$S1 = L, S0 = L, R_L = 680\Omega$		40			40		ns
t _{pd}	LEDB0 1	DB	$S1 = X, S0 = H, R_L = 680\Omega$		26			26		ns
t _{pd}	S1↑	СВ	$SO = H, R_L = 680\Omega$		40			40		ns
tPLH	OECB ↑	СВ	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns
t _{PHL}	<u>OECB</u> ↓	СВ	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns
t _{PLH}	OEB0 thru OEB3↑	DB	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns
t _{PHL}	OEB0 thru OEB3↓	DB	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns

†All typical values are at V_{CC} = 5V, T_A = +25°C.

Symbol	From (Input)	To (Output)	Test Conditions	Military			Commercial			Units
				Min	Typ†	Max	Min	Typ†	Max	Sills
t _{pd} DB and CB		ERR	$S1 = H, S0 = L, R_L = 500\Omega$		26			26		ns
		$S1 = L, S0 = H, R_L = 500\Omega$		26			26		115	
t _{pd} DB and CB	DB and CB	MERR	S1 = H, S0 = L, $R_L = 500\Omega$		40			40		ns
			$S1 = L, S0 = H, R_L = 500\Omega$		40			40		
t _{pd}	S0 \downarrow and S1 \downarrow	СВ	$R1=R2=500\Omega$		35			35		ns
t _{pd}	DB	СВ	$S1 = L, S0 = L, R1 = R2 = 500\Omega$		35			35		ns
t _{pd}	S1↑	СВ	$S0 = H, R1 = R2 = 500\Omega$		35			35		ns
t _{en}	OECB↓	СВ	$S1 = X, S0 = H, R1 = R2 = 500\Omega$		18			18		ns
t _{dis}	OECB ↑	СВ	$S1 = X, S0 = H, R1 = R2 = 500\Omega$		18			18		ns
t _{en}	OECB↓	DB	$S1 = X, S0 = H, R1 = R2 = 500\Omega$		18			18		ns
t _{dis}	OECB↑	DB	$S1 = X, S0 = H, R1 = R2 = 500\Omega$		18			18		ns

DP8405 Switching Characteristics, $V_{CC} = 4.5V$ to 5.5V, $C_L = 50$ pF, $T_A = Min$ to Max

Cumhal	From (Input)	To (Output)	Test Conditions	Military			Commercial			Units
Symbol				Min	Typ†	Max	Min	Typ†	Max	
	DB and CB	ERR	$S1 = H, S0 = L, R_L = 500\Omega$		26			26		ns
tpd	DB	ERR	$S1 = L, S0 = H, R_L = 500\Omega$		26			26		115
•	t _{pd} DB and CB	MERR	$S1 = H, S0 = L, R_L = 500\Omega$		40			40		ns
۰pa			$S1 = L, S0 = H, R_L = 500\Omega$		40			40		
t _{pd}	S0↓ and S1↓	СВ	$R_L = 680\Omega$		40			40		ns
t _{pd}	DB	СВ	$S1 = L, S0 = L, R_L = 680\Omega$		40			40		ns
t _{pd}	S1↑	DB	$SO = H, R_L = 680\Omega$		40			40		ns
t _{PLH}	OECB ↑	СВ	$S1 = X, S0 = H, R_L = 500\Omega$		24			24		ns
t _{PHL}	<u>OECB</u> ↓	СВ	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns
^t PLH		DB	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns
t _{PHL}		DB	$S1 = X, S0 = H, R_L = 680\Omega$		24			24		ns

†All typical values are at $V_{CC} = 5V$, $T_A = +25^{\circ}C$.



Switching Waveforms (Continued)





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